

L Number	Hits	Search Text	DB	Time stamp
64	34	diffusion with adjacent with (vertical adj transfer register) and CCD	USPAT	2004/03/19 10:34
71	154	CCD and lateral adj drain	USPAT	2004/03/19 10:49
72	8	CCD and lateral adj drain	USPAT	2004/03/19 10:51
74	101	vertical adj transfer with drain and CCD!	USPAT	2004/03/19 10:51
75	97	vertical adj transfer with drain and CCD! and @ay<2000	USPAT	2004/03/19 10:52
76	21	vertical adj transfer with drain same (voltage bias) and CCD! and @ay<2000	USPAT	2004/03/19 10:52
66	145	348/314.cccls.	USPAT	2004/03/19 11:01
80	64	348/314.cccls. and voltage with drain	USPAT	2004/03/19 11:09
81	87	voltage with substrate with potential with fluctuat\$5	USPAT	2004/03/19 11:10
82	10	voltage with substrate with potential with fluctuat\$5 and CCD	USPAT	2004/03/19 11:13
86	27	substrate with contact with (register vertical adj transfer) and CCD!	USPAT	2004/03/19 11:13
-	342	348/294.cccls.	USPAT	2004/03/16 09:35
-	195	348/302.cccls.	USPAT	2004/02/02 08:55
-	96	348/303.cccls.	USPAT	2004/02/02 08:55
-	80	348/304.cccls.	USPAT	2004/02/02 08:55
-	240	348/311.cccls.	USPAT	2004/02/02 10:07
-	37	348/323.cccls.	USPAT	2004/02/02 10:07
-	49	348/324.cccls.	USPAT	2004/02/02 10:07
-	18	(348/294.cccls. 348/302.cccls. 348/303.cccls. 348/304.cccls. 348/311.cccls. 348/322.cccls. 348/323.cccls. 348/324.cccls.) and wir\$3 adj layer	USPAT	2004/02/02 10:20
-	27	CCD and wir\$3 adj layer with transfer\$3	USPAT	2004/02/02 10:20
-	245	348/311.cccls.	USPAT	2004/03/15 12:32
-	88	348/315.cccls.	USPAT	2004/03/15 12:33
-	70	348/315.cccls. not 348/311.cccls.	USPAT	2004/03/15 12:40
-	103	348/322.cccls. not (348/311.cccls. 348/315.cccls.)	USPAT	2004/03/15 12:40
-	9	4847692.URPN.	USPAT	2004/03/15 16:06
-	6	("4336556" "4514766" "4577233" "4638362" "4652925" "4774586").PN.	USPAT	2004/03/15 16:31
-	263	257/232.cccls.	USPAT	2004/03/16 10:33
-	12	(smear and ccd).ti.	USPAT	2004/03/19 10:32
-	25	(US-5424775-\$ or US-5345099-\$ or US-5355165-\$ or US-4847692-\$ or US-4758894-\$ or US-4194213-\$ or US-4796072-\$ or US-4737833-\$ or US-5998808-\$ or US-5661317-\$ or US-6583558-\$ or US-6618088-\$ or US-6380977-\$ or US-6278487-\$ or US-5801850-\$ or US-5703640-\$ or US-5591660-\$ or US-5612739-\$ or US-5608205-\$ or US-5504355-\$ or US-5432551-\$ or US-5376811-\$ or US-5250825-\$ or US-5028970-\$ or US-4672455-\$).did.	USPAT	2004/03/16 15:19
-	5	((US-5424775-\$ or US-5345099-\$ or US-5355165-\$ or US-4847692-\$ or US-4758894-\$ or US-4194213-\$ or US-4796072-\$ or US-4737833-\$ or US-5998808-\$ or US-5661317-\$ or US-6583558-\$ or US-6618088-\$ or US-6380977-\$ or US-6278487-\$ or US-5801850-\$ or US-5703640-\$ or US-5591660-\$ or US-5612739-\$ or US-5608205-\$ or US-5504355-\$ or US-5432551-\$ or US-5376811-\$ or US-5250825-\$ or US-5028970-\$ or US-4672455-\$).did.) and smear	USPAT	2004/03/16 15:24
-	50	(((smear and CCD) and wir\$3) and via) and transfer) and (block shield)) and electrode	USPAT	2004/03/16 15:48
-	3	5442396.URPN.	USPAT	2004/03/16 15:48
-	212	CCD and (wir\$3 via) with (shield block) with light	USPAT	2004/03/16 15:53
-	163	CCD and (via) with (shield block) with light	USPAT	2004/03/16 15:53
-	1	CCD and (via with metal) with (shield block) with light	USPAT	2004/03/16 15:54
-	6	CCD and (via with hole) with (shield block) with light	USPAT	2004/03/16 15:55
-	10	CCD and (metal with hole) with (shield block) with light	USPAT	2004/03/16 15:55
-	120	348/322.cccls.	USPAT	2004/03/16 16:34

-	14998	(poly adj si polysilicon poly adj silicon) with metal	USPAT	2004/03/18 13:00
-	360	(poly adj si polysilicon poly adj silicon) with metal with instead	USPAT	2004/03/18 13:04
-	0	(poly adj si polysilicon poly adj silicon) with metal with instead with because	USPAT	2004/03/18 13:11
-	158	CCD and substrate with bias same transfer	USPAT	2004/03/18 13:14
-	19	CCD and substrate same (voltage bias\$2) same diffusion adj area	USPAT	2004/03/18 15:58
-	347	substrate same bias same saturation	USPAT	2004/03/18 16:00
-	22	substrate same bias same saturation same diffusion	USPAT	2004/03/18 16:02
-	527	CCD and diffusion same transfer same (voltage bias)	USPAT	2004/03/18 16:28
-	32	CCD and diffusion same transfer same (voltage bias) same contact	USPAT	2004/03/18 16:28
-	342	257/233.ccls.	USPAT	2004/03/19 10:17
-	2	CCD and substrate adj (voltage contact bias) with vertical adj transfer	USPAT	2004/03/18 17:26
-	53	CCD and substrate adj (voltage contact bias) with transfer	USPAT	2004/03/18 17:26
-	7	257/233.ccls. and vertical adj transfer and substrate adj (bias voltage)	USPAT	2004/03/19 10:19
-	4	257/232.ccls. and vertical adj transfer and substrate adj (bias voltage)	USPAT	2004/03/19 10:20
-	20	348/294-324.ccls. and vertical adj transfer and substrate adj (bias voltage)	USPAT	2004/03/19 10:21